Dual decade ripple counter Rev. 3 — 16 August 2016

Product data sheet

#### **General description** 1.

The 74HC390; 74HCT390 is a dual 4-bit decade ripple counter divided into four separately clocked sections. The counters have two divide-by-2 sections and two divide-by-5 sections. These sections share an asynchronous master reset input (nMR) and can be used in a BCD decade or bi-quinary configuration. If master reset inputs 1MR and 2MR are used to clear all 8 bits of the counter simultaneously, numerous counting configurations are possible within one package. Section clocks nCP0 and nCP1, allow ripple counter or frequency division applications of divide-by-2, 4, 5, 10, 20, 25, 50 or 100. The HIGH-to-LOW transition of the clock inputs nCP0 and nCP1 trigger each section. For BCD decade operation, the nQ0 output is connected to the nCP1 input of the divide-by-5 section. For bi-quinary decade operation, the nQ3 output is connected to the nCP0 input and nQ0 becomes the decade output. A HIGH on the nMR input overrides the clocks and sets the four outputs LOW. Inputs include clamp diodes. It enables the use of current limiting resistors to interface inputs to voltages in excess of V<sub>CC</sub>.

#### Features and benefits 2.

- Input levels:
  - For 74HC390: CMOS level
  - For 74HCT390: TTL level
- Two BCD decade or bi-quinary counters
- One device can be configured to divide-by-2, 4, 5, 10, 20, 25, 50 or 100
- Two master reset inputs to clear each decade counter individually
- Specified in compliance with JEDEC standard no. 7A
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from –40 °C to +85 °C and from –40 °C to +125 °C

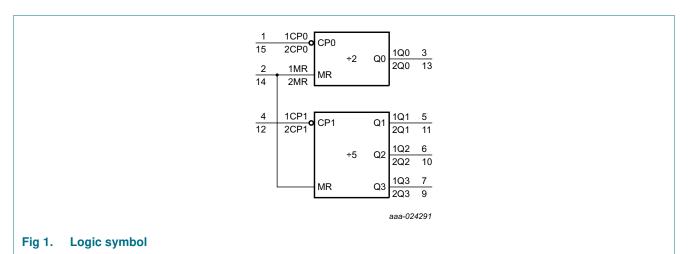


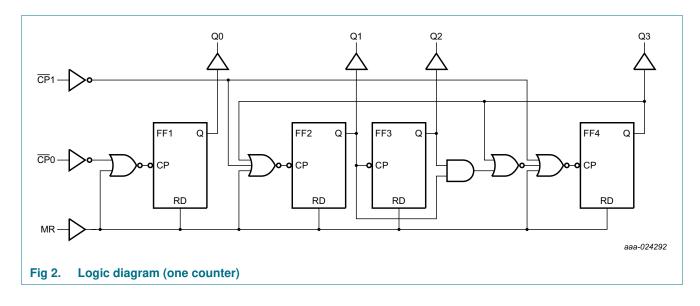
### 3. Ordering information

#### Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC390D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT390D				
74HC390DB	–40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads;	SOT338-1
74HCT390DB			body width 5.3 mm	
74HCT390PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

## 4. Functional diagram

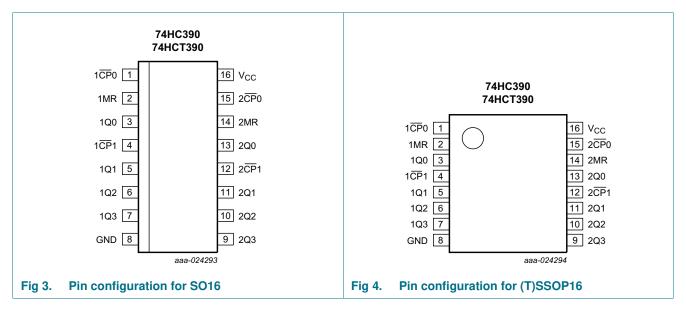




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### 5. Pinning information

### 5.1 Pinning



### 5.2 Pin description

### Table 2. Pin description

Symbol	Pin	Description
1 <u>CP</u> 0, 2 <u>CP</u> 0	1, 15	clock input divide-by-2 section (HIGH-to-LOW; edge-triggered)
1MR, 2MR	2, 14	asynchronous master reset input (active HIGH)
1Q0, 1Q1, 1Q2, 1Q3	3, 5, 6, 7	flip-flop outputs
1 <u>CP</u> 1, 2 <u>CP</u> 1	4, 12	clock input divide-by-5 section (HIGH-to-LOW; edge-triggered)
GND	8	ground (0 V)
2Q0, 2Q1, 2Q2, 2Q3	13, 11, 10, 9	flip-flop outputs
V <sub>CC</sub>	16	supply voltage

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### 6. Functional description

Count	Output				
	nQ0	nQ1	nQ2	nQ3	
0	L	L	L	L	-
1	Н	L	L	L	
2	L	Н	L	L	
3	Н	Н	L	L	
4	L	L	Н	L	
5	Н	L	Н	L	
6	L	Н	Н	L	
7	Н	Н	Н	L	
8	L	L	L	Н	
9	Н	L	L	Н	

[1] Output nQ0 connected to  $n\overline{CP1}$ ; counter input on  $n\overline{CP0}$ .

H = HIGH voltage level

L = LOW voltage level

#### Table 4. Bi-quinary count sequence<sup>[1]</sup>

Count	Output			
	nQ0	nQ1	nQ2	nQ3
0	L	L	L	L
1	L	Н	L	L
2	L	L	Н	L
3	L	Н	Н	L
4	L	L	L	Н
5	Н	L	L	L
6	Н	Н	L	L
7	Н	L	Н	L
8	Н	Н	Н	L
9	Н	L	L	Н

[1] Output nQ3 connected to  $n\overline{CP}0$ ; counter input on  $n\overline{CP}1$ .

H = HIGH voltage level

L = LOW voltage level

### 7. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC</sub>	supply voltage			-0.5	+7	V
I <sub>IK</sub>	input clamping current	$V_{\rm I} < -0.5$ V or $V_{\rm I} > V_{\rm CC}$ + 0.5 V		-	±20	mA
I <sub>OK</sub>	output clamping current	$V_{\rm O}$ < -0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V		-	±20	mA
lo	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$		-	±25	mA
I <sub>CC</sub>	supply current			-	+50	mA
I <sub>GND</sub>	ground current			-50	-	mA
T <sub>stg</sub>	storage temperature			-65	+150	°C
P <sub>tot</sub>	total power dissipation	SO16 and (T)SSOP16 packages	<u>[1]</u>	-	500	mW

## 8. Recommended operating conditions

#### Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	Conditions 74HC390		7	4HCT39	0	Unit	
			Min	Тур	Max	Min	Тур	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
Vo	output voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

### 9. Static characteristics

#### Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C	;	–40 °C t	o +85 °C	–40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC390	)									
V <sub>IH</sub>	HIGH-level	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	3.15	-	V
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V <sub>IL</sub>	LOW-level	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	V <sub>CC</sub> = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V

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#### Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C	;	–40 °C t	o +85 °C	–40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
V <sub>OH</sub>	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_{O} = -20 \ \mu A; V_{CC} = 2.0 \ V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_{O} = -20 \ \mu A; V_{CC} = 4.5 \ V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -20 \ \mu A; V_{CC} = 6.0 \ V$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V <sub>OL</sub>	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_{O} = 20 \ \mu A; V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 20 \ \mu A; V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 20 \ \mu A; V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_0 = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
lı	input leakage current	$V_{I} = V_{CC}$ or GND; $V_{CC} = 6.0 V$	-	-	±0.1	-	±1	-	±1	μA
l <sub>cc</sub>	supply current		-	-	8.0	-	80	-	160	μA
CI	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT3	90									
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
VIL	LOW-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -4.0 mA	3.98	4.32	-	3.84	-	3.7	-	V
V <sub>OL</sub>	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								-
	output voltage	$I_{O} = 20 \ \mu A; V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 5.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
I	input leakage current	$V_{I} = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	±0.1	-	±1	-	±1	μA
I <sub>CC</sub>	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 5.5 \ V \end{array}$	-	-	8.0	-	80	-	160	μA
∆I <sub>CC</sub>	additional supply current	per input pin; $V_1 = V_{CC} - 2.1 V$ ; other inputs at $V_{CC}$ or GND; $V_{CC} = 4.5 V$ to 5.5 V								
		nCP0 inputs	-	45	162	-	202.5	-	220.5	μA
		nCP1, nMR inputs	-	60	216	-	270	-	294	μA
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

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## **10. Dynamic characteristics**

#### Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V);  $C_L = 50 \text{ pF}$  unless otherwise specified; for test circuit, see Figure 7.

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C t	o +125 °C	Unit
			Min	Typ[1]	Max	Min	Мах	Min	Max	
74HC39	0					1		1		
t <sub>pd</sub>	propagation	nCP0 to nQ0; see Figure 5 [2]								
	delay	V <sub>CC</sub> = 2.0 V	-	47	145	-	180	-	220	ns
		V <sub>CC</sub> = 4.5 V	-	17	29	-	36	-	44	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	14	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	14	25	-	31	-	38	ns
		nCP1 to nQ1; see Figure 5								
		V <sub>CC</sub> = 2.0 V	-	50	155	-	195	-	235	ns
		V <sub>CC</sub> = 4.5 V	-	18	31	-	39	-	47	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	15	-	-	-	-	-	ns
		$V_{\rm CC} = 6.0 \ V$	-	14	26	-	33	-	40	ns
		nCP1 to nQ2; see Figure 5								
		V <sub>CC</sub> = 2.0 V	-	74	210	-	265	-	315	ns
		V <sub>CC</sub> = 4.5 V	-	27	42	-	53	-	63	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	23	-	-	-	-	-	ns
		$V_{\rm CC} = 6.0 \ V$	-	22	36	-	45	-	54	ns
		nCP1 to nQ3; see Figure 5								
		V <sub>CC</sub> = 2.0 V	-	50	155	-	195	-	235	ns
		V <sub>CC</sub> = 4.5 V	-	18	31	-	39	-	47	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	15	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	14	26	-	33	-	40	ns
t <sub>PHL</sub>	HIGH to LOW	nMR to nQn; see Figure 6								-
	propagation	V <sub>CC</sub> = 2.0 V	-	52	165	-	205	-	250	ns
	delay	V <sub>CC</sub> = 4.5 V	-	19	33	-	41	-	50	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	16	-	-	-	-	-	ns
		V <sub>CC</sub> = 6.0 V	-	15	28	-	35	-	43	ns
t <sub>t</sub>	transition	nQn; see <u>Figure 5</u> [3]								
	time	V <sub>CC</sub> = 2.0 V	-	19	75	-	95	-	110	ns
		V <sub>CC</sub> = 4.5 V	-	7	15	-	19	-	22	ns
		$V_{\rm CC} = 6.0 \text{ V}$	-	6	13	-	16	-	19	ns

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Symbol	Parameter	Conditions		25 °C		–40 °C to	o +85 °C	–40 °C t	o +125 °C	Unit
-			Min	Typ[1]	Max	Min	Max	Min	Max	-
tw	pulse width	nCP0, nCP1; HIGH or LOW; see <u>Figure 5</u>								
		V <sub>CC</sub> = 2.0 V	80	19	-	100	-	120	-	ns
		V <sub>CC</sub> = 4.5 V	16	7	-	20	-	24	-	ns
		V <sub>CC</sub> = 6.0 V	14	6	-	17	-	20	-	ns
		nMR HIGH; see Figure 6								
		V <sub>CC</sub> = 2.0 V	80	28	-	105	-	130	-	ns
		V <sub>CC</sub> = 4.5 V	17	10	-	21	-	26	-	ns
		V <sub>CC</sub> = 6.0 V	14	8	-	18	-	22	-	ns
rec	recovery time	nMR to nCPn; see <u>Figure 6</u>								
		V <sub>CC</sub> = 2.0 V	75	22	-	95	-	110	-	ns
		V <sub>CC</sub> = 4.5 V	15	8	-	19	-	22	-	ns
		V <sub>CC</sub> = 6.0 V	13	6	-	16	-	19	-	ns
f <sub>max</sub>	maximum	nCPn; see <u>Figure 5</u>								
	frequency	V <sub>CC</sub> = 2.0 V	6.0	20	-	4.8	-	4.0	-	MH
		V <sub>CC</sub> = 4.5 V	30	60	-	24	-	20	-	MH
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	66	-	-	-	-	-	MH
		V <sub>CC</sub> = 6.0 V	35	71	-	28	-	24	-	MH
C <sub>PD</sub>	power dissipation capacitance	$\begin{array}{ll} C_L = 50 \text{ pF; } f = 1 \text{ MHz;} & \ensuremath{\underline{[4]}} \\ V_I = GND \text{ to } V_{CC} \end{array}$	-	20	-	-	-	-	-	pF
74HCT39	90			1		1				
t <sub>pd</sub>	propagation	nCP0 to nQ0; see Figure 5 [2]								
	delay	V <sub>CC</sub> = 4.5 V	-	21	34	-	43	-	51	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	18	-	-	-	-	-	ns
		nCP1 to nQ1; see Figure 5								
		V <sub>CC</sub> = 4.5 V	-	22	38	-	48	-	57	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	19	-	-	-	-	-	ns
		nCP1 to nQ2; see Figure 5								
		V <sub>CC</sub> = 4.5 V	-	30	51	-	64	-	77	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	26	-	-	-	-	-	ns
		nCP1 to nQ3; see Figure 5								
		V <sub>CC</sub> = 4.5 V	-	22	38	-	48	-	57	ns
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	19	-	-	-	-	-	ns
PHL	HIGH to LOW	nMR to nQn; see Figure 6								
	propagation	V <sub>CC</sub> = 4.5 V	-	21	36	-	45	-	54	ns
	delay	V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	18	-	-	-	-	-	ns
t	transition	nQn; see <u>Figure 5</u> [3]								
	time		1	1	1	1	1	1	1	1

#### **Dynamic characteristics** ...continued e referenced to GND (around = 0.V): C Table 8.

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Dual decade ripple counter

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C t	o +125 °C	Unit
			Min	Typ[1]	Max	Min	Max	Min	Max	-
tw	pulse width	nCP0, nCP1; HIGH or LOW; see <u>Figure 5</u>								
		V <sub>CC</sub> = 4.5 V	18	8	-	23	-	27	-	ns
		nMR HIGH; see Figure 6								
		V <sub>CC</sub> = 4.5 V	17	10	-	21	-	26	-	ns
t <sub>rec</sub>	recovery time	nMR to nCPn; see <u>Figure 6</u>								
		V <sub>CC</sub> = 4.5 V	15	8	-	19	-	22	-	ns
f <sub>max</sub>	maximum	nCPn; see Figure 5								
	frequency	V <sub>CC</sub> = 4.5 V	27	55	-	22	-	18	-	MHz
		V <sub>CC</sub> = 5 V; C <sub>L</sub> = 15 pF	-	61	-	-	-	-	-	MHz
C <sub>PD</sub>	power dissipation capacitance	$C_L = 50 \text{ pF}; f = 1 \text{ MHz};$ [4] V <sub>I</sub> = GND to V <sub>CC</sub> - 1.5 V	-	21	-	-	-	-	-	pF

#### Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V);  $C_L = 50 \text{ pF}$  unless otherwise specified; for test circuit, see Figure 7.

[1] All typical values are measured at  $T_{amb} = 25 \ ^{\circ}C$ .

[2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[3]  $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$ .

[4]  $C_{PD}$  is used to determine the dynamic power dissipation (P<sub>D</sub> in  $\mu$ W).

 $P_{D} = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \sum (C_L \times V_{CC}{}^2 \times f_o)$  where:

 $f_i$  = input frequency in MHz;

 $f_o$  = output frequency in MHz;

 $C_L$  = output load capacitance in pF;

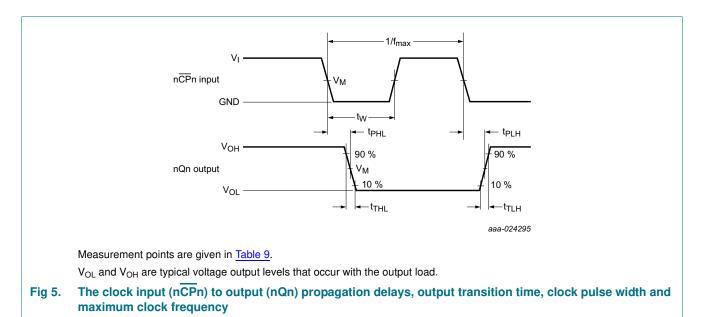
 $V_{CC}$  = supply voltage in V;

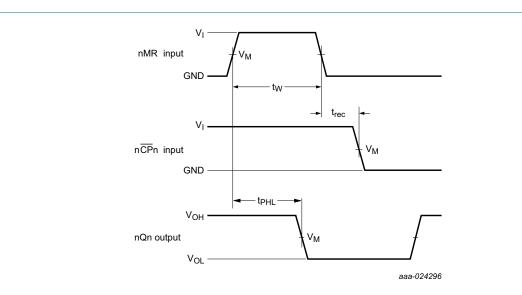
N = number of inputs switching;  $\Sigma(2 - 1)(-2 - 1)$ 

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$  = sum of outputs.

Dual decade ripple counter

### 11. Waveforms





Measurement points are given in Table 9.

 $V_{\text{OL}}$  and  $V_{\text{OH}}$  are typical voltage output levels that occur with the output load.

## Fig 6. The master reset (nMR) pulse width, master reset to output (nQn) propagation delays and master reset to clock (nCPn) recovery time

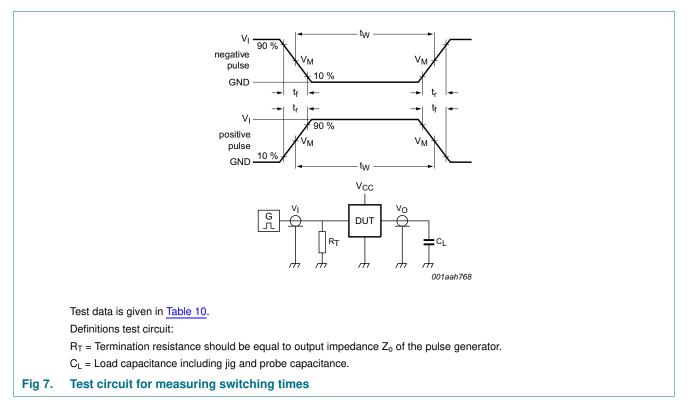
#### Table 9.Measurement points

Туре	Input	Output
	V <sub>M</sub>	V <sub>M</sub>
74HC390	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>
74HCT390	1.3 V	1.3 V

### **NXP Semiconductors**

## 74HC390; 74HCT390

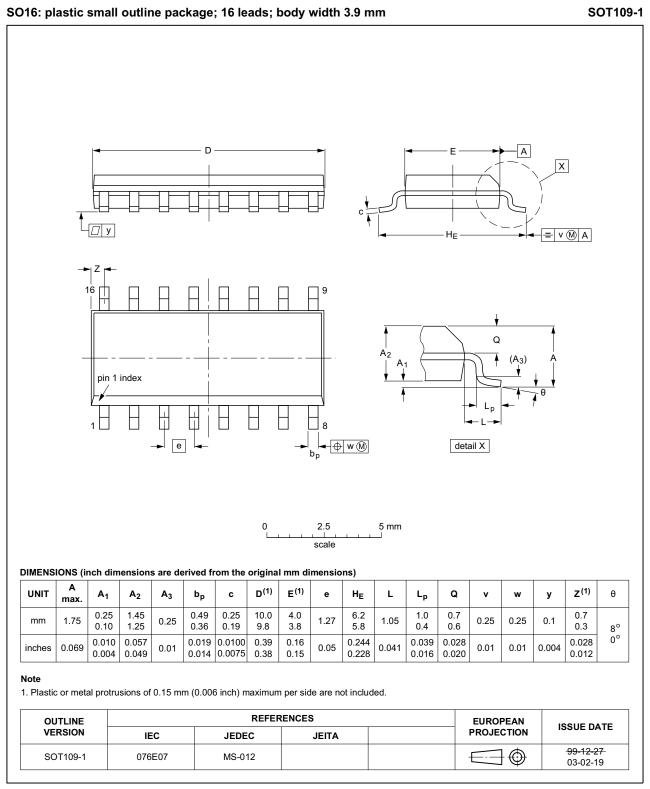
### Dual decade ripple counter



#### Table 10. Test data

Туре	Input		Load	Test
	VI	t <sub>r</sub> , t <sub>f</sub>	CL	
74HC390	V <sub>CC</sub>	6 ns	15 pF, 50 pF	t <sub>PLH</sub> , t <sub>PHL</sub>
74HCT390	3 V	6 ns	15 pF, 50 pF	t <sub>PLH</sub> , t <sub>PHL</sub>

### 12. Package outline



#### Package outline SOT109-1 (SO16) Fig 8.

74HC\_HCT390

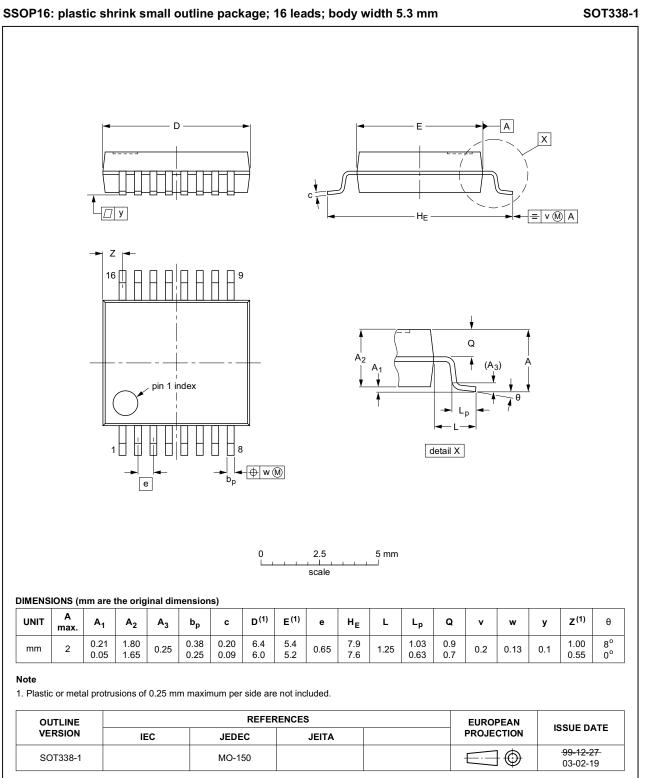


Fig 9. Package outline SOT338-1 (SSOP16)

74HC\_HCT390

Dual decade ripple counter

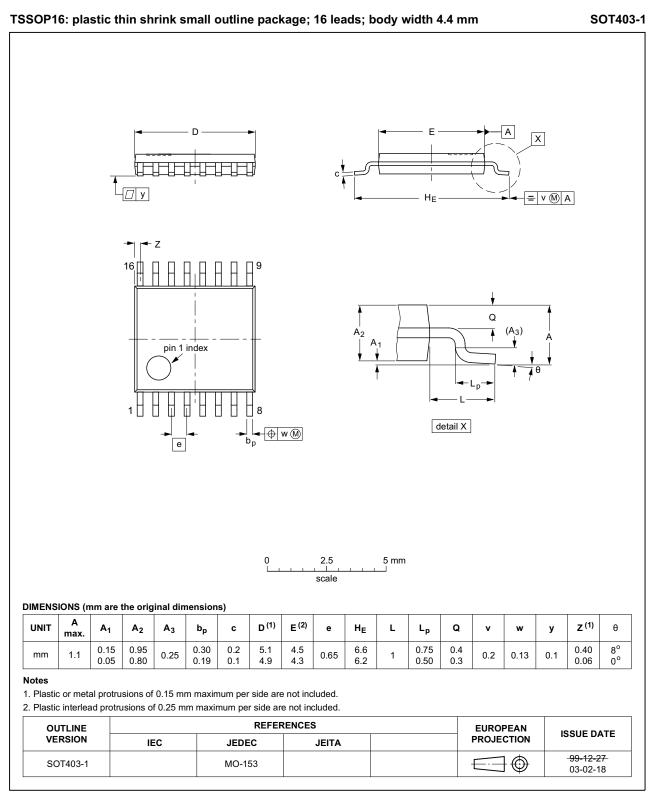


Fig 10. Package outline SOT403-1 (TSSOP16)

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## **13. Abbreviations**

Table 11. Abbreviations		
Acronym	Description	
CMOS	Complementary Metal Oxide Semiconductor	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
HBM	Human Body Model	
MM	Machine Model	
TTL	Transistor-Transistor Logic	

## 14. Revision history

### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT390 v.3	20160816	Product data sheet	-	74HC_HCT390_CNV v.2
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>			y with the new identity
	<ul> <li>Legal texts I</li> </ul>	have been adapted to the	new company name v	vhere appropriate.
	<ul> <li>Type numbers 74HC390N and 74HCT390N removed.</li> </ul>			
74HC_HCT390_CNV v.2	19901201	Product specification	-	-

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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